

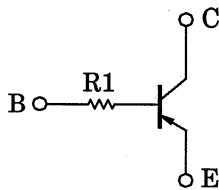
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2112F,RN2113F

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1112F, RN1113F

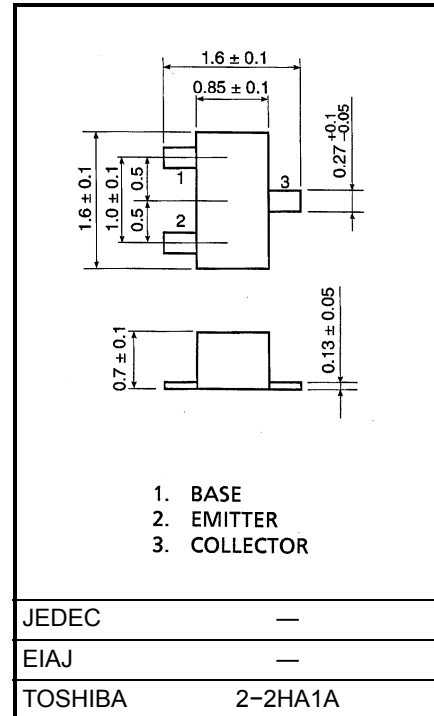
Equivalent Circuit



Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C	100	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55~150	°C

Unit in mm



Weight: 2.3 mg

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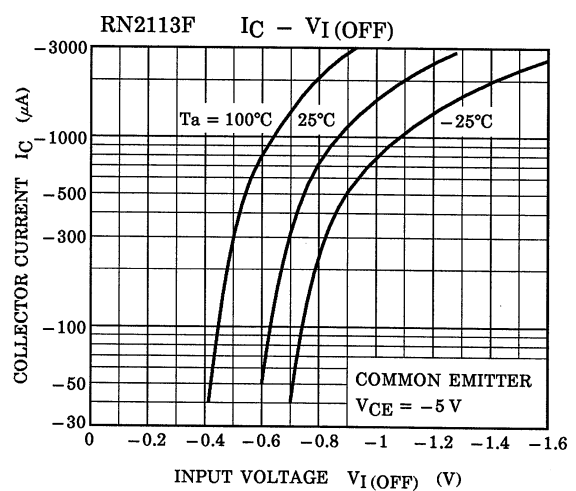
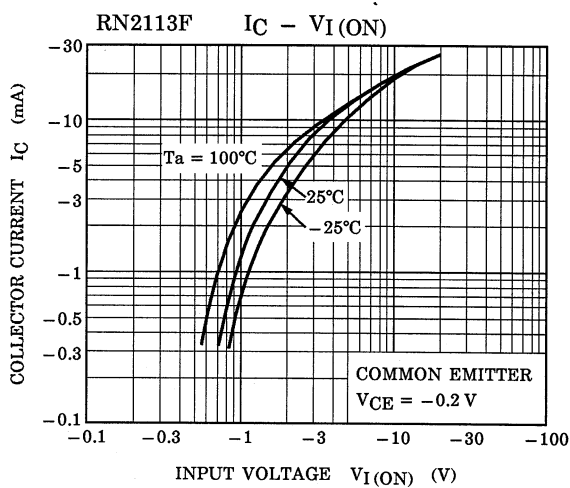
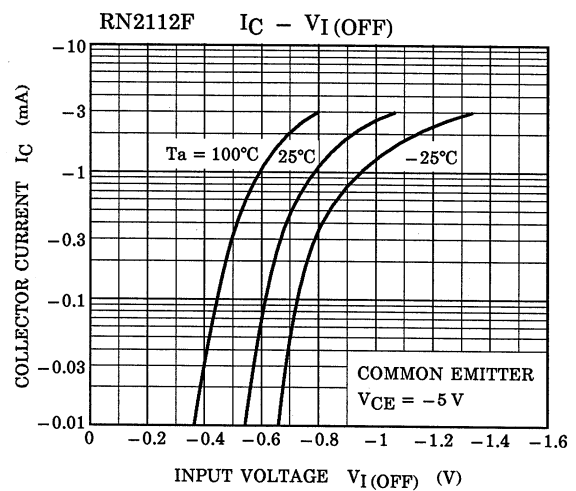
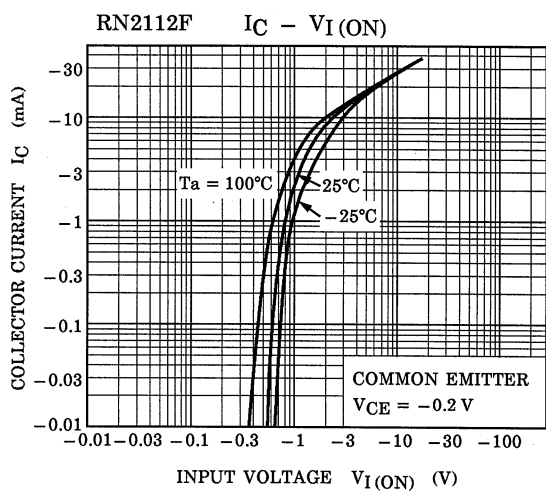
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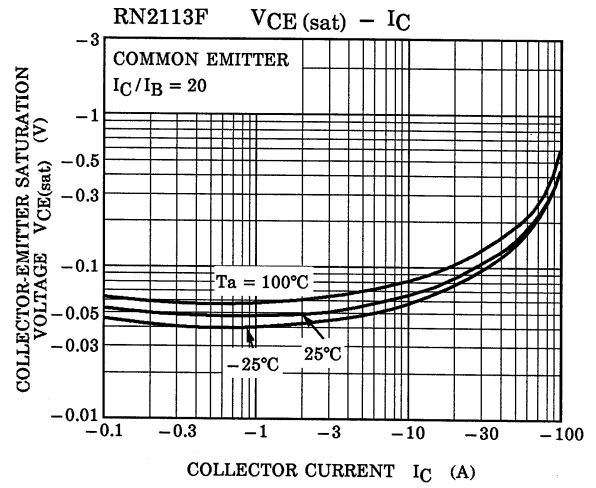
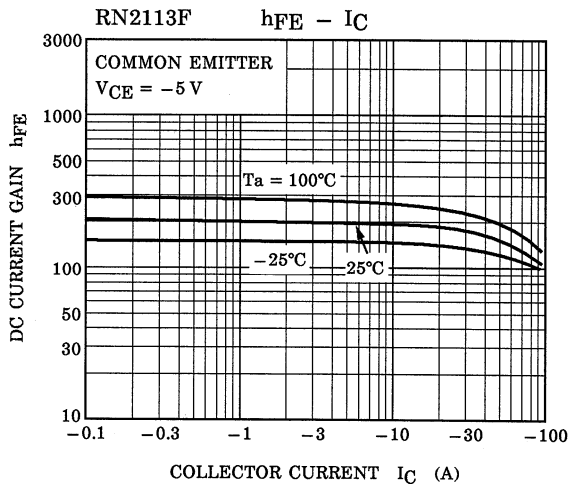
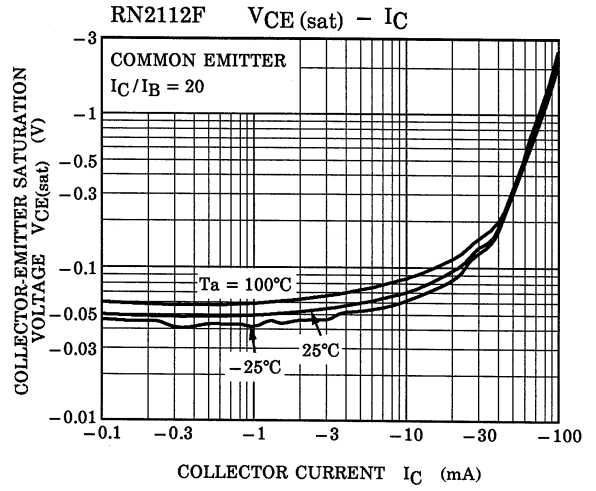
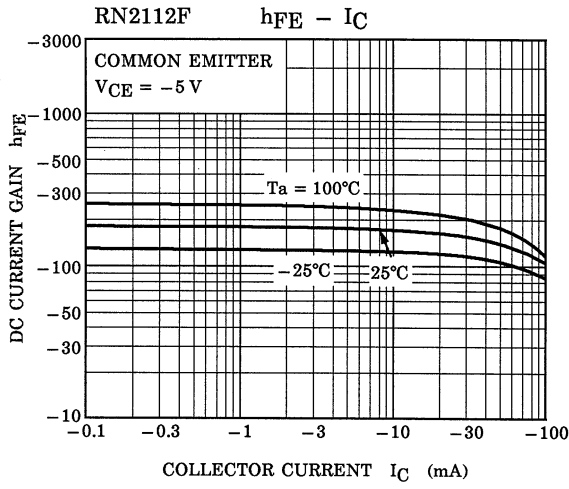
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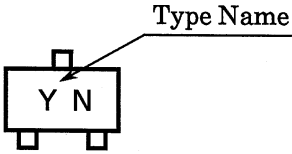
• The information contained herein is subject to change without notice.

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	—	$V_{CB} = -50V, I_E = 0$	—	—	-100	nA
Emitter cut-off current	I_{EBO}	—	$V_{EB} = -5V, I_C = 0$	—	—	-100	nA
DC current gain	h_{FE}	—	$V_{CE} = -5V, I_C = -1mA$	120	—	400	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	$I_C = -5mA, I_B = -0.25mA$	—	-0.1	-0.3	V
Transition frequency	f_T	—	$V_{CE} = -10V, I_C = -5mA$	—	200	—	MHz
Collector output capacitance	C_{ob}	—	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	3	6	pF
Input resistor	RN2112F	R1	—	15.4	22	28.6	k Ω
	RN2113F			32.9	47	61.1	





Type Name	Marking
RN2112F	
RN2113F	